

UNIVERSITY OF OXFORD

## J Wolf T P Harty C M Löschnauer M A Sepiol J F Goodwin J E Tarlton A C Hughes A M Steane D M Lucas Quantum logic gates driven by near-field microwaves

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Auvantages	field

- Features integrated microwave circuitry [Allcock et al. APL (2013)]

## Current two-qubit gate scheme



- Bichromatic field with frequencies near first red and blue sidebands as for Mølmer-Sørensen gates - Dynamical decoupling with a  $\sigma x$  carrier drive protects against fluctuations in AC Zeeman shift ( $\Delta \uparrow - \Delta \downarrow$ ) - Carrier drive Rabi frequency of 4kHz compared with 436Hz for single-ion sideband

-  $\pi$ [y] pulse at midpoint to refocus qubit populations

## Current two-qubit gate results



excitation

- Two-qubit gate fidelity of 99.7(1)% [Harty et al. Phys. Rev. Lett. 117, 140501 (2016)] - See also work done with far-field microwaves at Siegen [Khromova et al. PRL (2012)] and Sussex [Weidt et al. Phys. Rev. Lett. 117, 220501 (2016)]



 Plot shows the different two-qubit populations - as a function of microwave detuning from sidebands

- Dashed line indicates detuning used for gate - Compared with simulations to calibrate gate parameters

## Current DDMS gate: numerical simulations

 $T_2^* \approx 50 \text{ sec}$ 

99.98%

99.95%

99.7%v

99.9999%



- comparison between dynamically-decoupled Molmer-Sorensen (DDMS) gate and single-sideband Bermudez (SSB) gate
- simulation assumes 4-loop gate with sideband Rabi frequency  $\Omega/2\pi$  = 308 Hz, and uncompensated a.c. Zeeman shift of 20 Hz - vertical dashed line indicates the carrier Rabi frequency used in our experiment ( $\Omega_c/2\pi = 3.69 \text{ kHz}$ )



- Cryogenic cooling with Janis ST-400 cryostat
- Cold finger thermally connected to inner chamber with copper braid to minimise vibrational coupling
- Inner chamber attached to base of vacuum chamber with Macor supports to minimise thermal load
- Option for ex-situ argon ion surface cleaning

- Designed for 288gauss clock qubit:  $S_{1/2}$  (4,+1) $\leftrightarrow$ (3,+1)
- Concept: "U-shaped" microwave drive electrode to null  $\pi$ -field along quantisation axis  $(B_0)$  direction by geometry [see Carjens et al. App.
- Phys. B (2014) for alternative geometry]
- Not necessary to null σ-field for high-fidelity DDMS gate
- On-chip microwave resonator to increase field strength



- Design goal: microwave  $\pi$ -field gradient of > 30 T/m, with  $\pi$ -field nulled to < 30  $\mu$ T - Should allow DDMS gate with up to an order of magnitude improvement in speed and error over previous trap

